

DATA SHEET

74ABT10 Triple 3-input NAND gate

Product specification

1995 Sep 22

IC23 Data Handbook

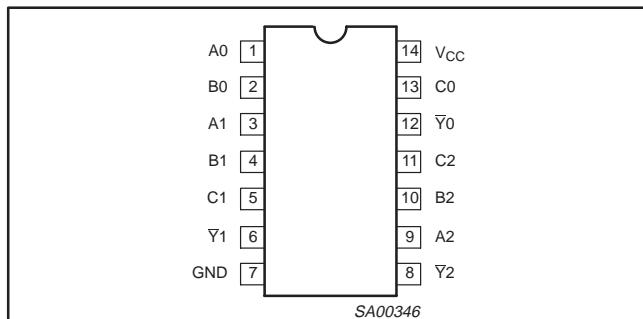
Triple 3-input NAND gate

74ABT10

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS $T_{amb} = 25^\circ\text{C}$; $\text{GND} = 0\text{V}$	TYPICAL	UNIT
t_{PLH} t_{PHL}	Propagation delay An, Bn, Cn to \bar{Y}_n	$C_L = 50\text{pF};$ $V_{CC} = 5\text{V}$	3.3 2.2	ns
			0.4	ns
C_{IN}	Input capacitance	$V_I = 0\text{V}$ or V_{CC}	3	pF
I_{CC}	Total supply current	Outputs disabled; $V_{CC} = 5.5\text{V}$	50	μA

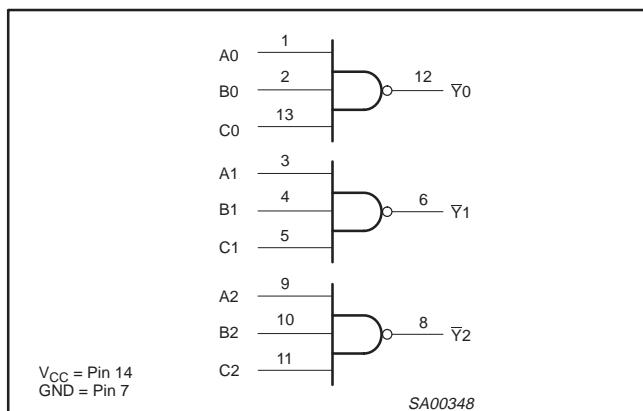
PIN CONFIGURATION



PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 2, 3, 4, 5, 9, 10, 11, 13	An, Bn, Cn	Data inputs
6, 8, 12	\bar{Y}_n	Data outputs
7	GND	Ground (0V)
14	V_{CC}	Positive supply voltage

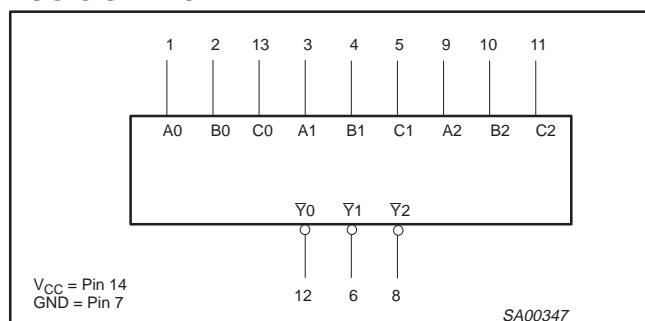
LOGIC DIAGRAM



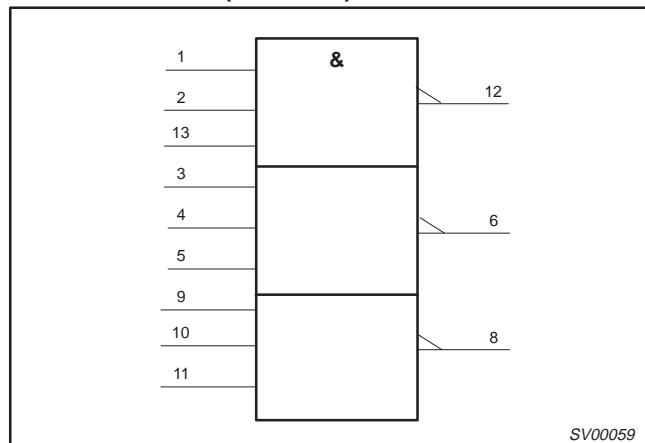
ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
14-Pin Plastic DIP	-40°C to +85°C	74ABT10 N	74ABT10 N	SOT27-1
14-Pin plastic SO	-40°C to +85°C	74ABT10 D	74ABT10 D	SOT108-1
14-Pin Plastic SSOP Type II	-40°C to +85°C	74ABT10 DB	74ABT10 DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +85°C	74ABT10 PW	74ABT10PW DH	SOT402-1

LOGIC SYMBOL



LOGIC SYMBOL (IEEE/IEC)



FUNCTION TABLE

INPUTS			OUTPUTS
An	Bn	Cn	\bar{Y}_n
L	L	L	H
L	L	H	H
L	H	L	H
L	H	H	H
H	L	L	H
H	L	H	H
H	H	L	H
H	H	H	L

NOTES:

H = High voltage level
L = Low voltage level

Triple 3-input NAND gate

74ABT10

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V_{CC}	DC supply voltage		-0.5 to +7.0	V
I_{IK}	DC input diode current	$V_I < 0$	-18	mA
V_I	DC input voltage ³		-1.2 to +7.0	V
I_{OK}	DC output diode current	$V_O < 0$	-50	mA
V_{OUT}	DC output voltage ³	output in Off or High state	-0.5 to +5.5	V
I_{OUT}	DC output current	output in Low state	40	mA
T_{stg}	Storage temperature range		-65 to 150	°C

NOTES:

- Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.
- The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMITS		UNIT
		MIN	MAX	
V_{CC}	DC supply voltage	4.5	5.5	V
V_I	Input voltage	0	V_{CC}	V
V_{IH}	High-level input voltage	2.0		V
V_{IL}	Low-level input voltage		0.8	V
I_{OH}	High-level output current		-15	mA
I_{OL}	Low-level output current		20	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T_{amb}	Operating free-air temperature range	-40	+85	°C

DC ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT		
			$T_{amb} = +25^\circ\text{C}$		$T_{amb} = -40^\circ\text{C}$ to $+85^\circ\text{C}$			
			MIN	Typ	MAX			
V_{IK}	Input clamp voltage	$V_{CC} = 4.5\text{V}$; $I_{IK} = -18\text{mA}$		-0.9	-1.2		-1.2	V
V_{OH}	High-level output voltage	$V_{CC} = 4.5\text{V}$; $I_{OH} = -15\text{mA}$; $V_I = V_{IL}$ or V_{IH}	2.5	2.9		2.5		V
V_{OL}	Low-level output voltage	$V_{CC} = 4.5\text{V}$; $I_{OL} = 20\text{mA}$; $V_I = V_{IL}$ or V_{IH}	0.35	0.5		0.5		V
I_I	Input leakage current	$V_{CC} = 5.5\text{V}$; $V_I = \text{GND}$ or 5.5V	± 0.01	± 1.0		± 1.0		μA
I_{OFF}	Power-off leakage current	$V_{CC} = 0.0\text{V}$; V_O or $V_I \leq 4.5\text{V}$	± 5.0	± 100		± 100		μA
I_{CEX}	Output High leakage current	$V_{CC} = 5.5\text{V}$; $V_O = 5.5\text{V}$; $V_I = \text{GND}$ or V_{CC}	5.0	50		50		μA
I_O	Output current ¹	$V_{CC} = 5.5\text{V}$; $V_O = 2.5\text{V}$	-50	-75	-180	-50	-180	mA
I_{CC}	Quiescent supply current	$V_{CC} = 5.5\text{V}$; $V_I = \text{GND}$ or V_{CC}		2	50		50	μA
ΔI_{CC}	Additional supply current per input pin ²	$V_{CC} = 5.5\text{V}$; One data input at 3.4V , other inputs at V_{CC} or GND		0.25	500		500	μA

NOTES:

- Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
- This is the increase in supply current for each input at 3.4V .
- For valid test results, data must not be loaded into the flip-flop or latch after applying the power.

Triple 3-input NAND gate

74ABT10

AC CHARACTERISTICS

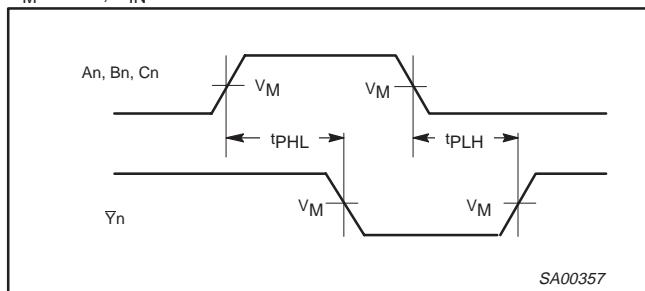
 $V_{DD} = 0V$; $t_R = t_F = 2.5\text{ns}$; $C_L = 50\text{pF}$, $R_L = 500\Omega$

SYMBOL	PARAMETER	WAVEFORM	LIMITS					UNIT	
			$T_{amb} = +25^\circ\text{C}$ $V_{CC} = +5.0\text{V}$			$T_{amb} = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = +5.0\text{V} \pm 0.5\text{V}$			
			MIN	TYP	MAX	MIN	MAX		
t_{PLH} t_{PHL}	Propagation delay An, Bn, Cn to \bar{Y}_n	1	1.0 1.0	3.3 2.2	4.7 3.3	1.0 1.0	5.3 3.7	ns	
t_{OSHL} t_{OSLH} ¹	Output to Output skew An or Bn to \bar{Y}_n	2		0.4	0.5		0.5	ns	

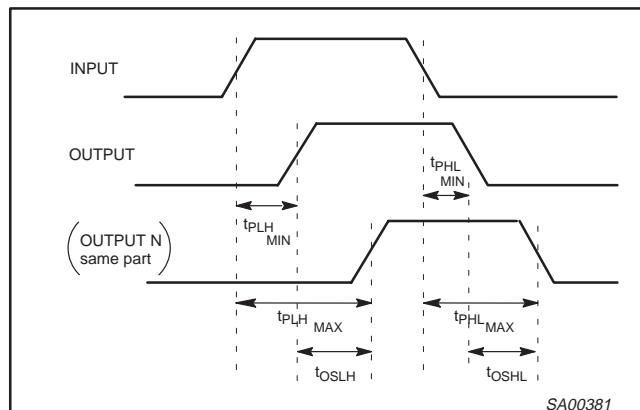
NOTE:

1. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

AC WAVEFORMS

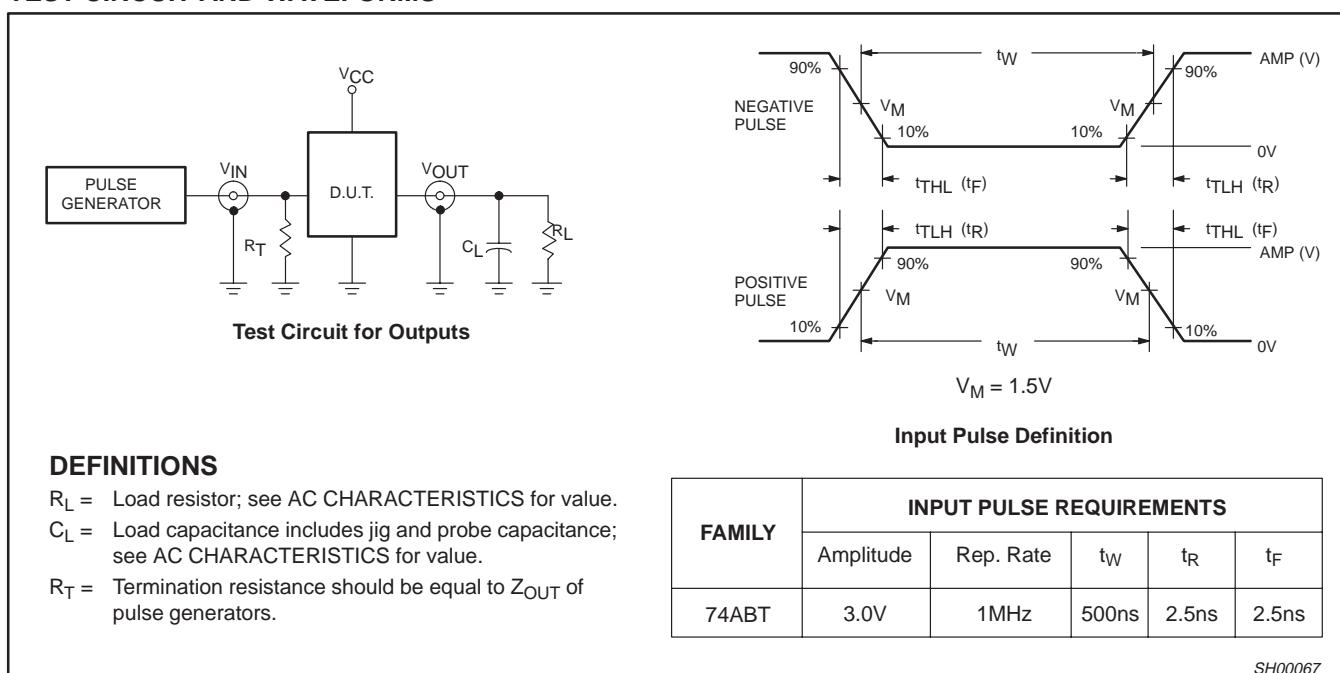
 $V_M = 1.5\text{V}$, $V_{IN} = \text{GND}$ to 3.0V 

Waveform 1. Propagation Delay for Inverting Outputs



Waveform 2. Common edge skew

TEST CIRCUIT AND WAVEFORMS

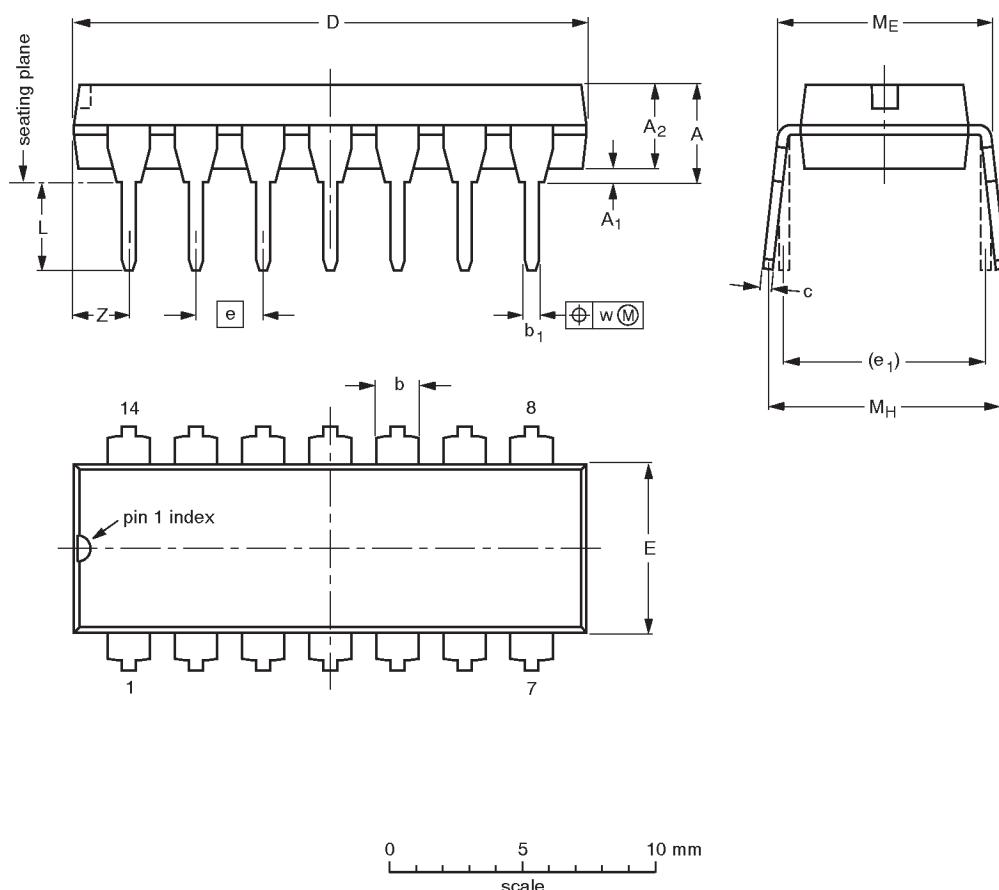


Triple 3-input NAND gate

74ABT10

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	M _E	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

- Plastic or metal protrusions of 0.25 mm maximum per side are not included.

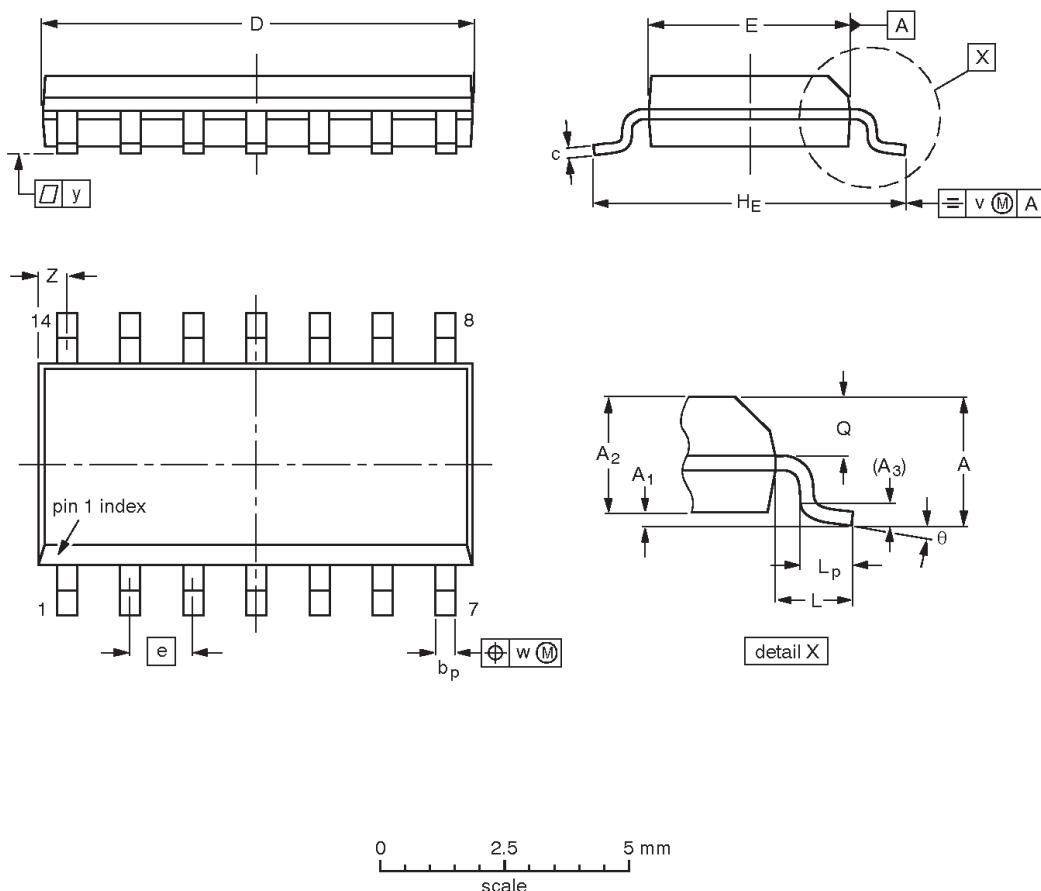
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT27-1	050G04	MO-001AA				92-11-17 95-03-11

Triple 3-input NAND gate

74ABT10

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.75 0.10	0.25 1.25	1.45	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069 0.004	0.010 0.049	0.057	0.01	0.019 0.014	0.0100 0.0075	0.35 0.34	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Note

- Plastic or metal protrusions of 0.15 mm maximum per side are not included.

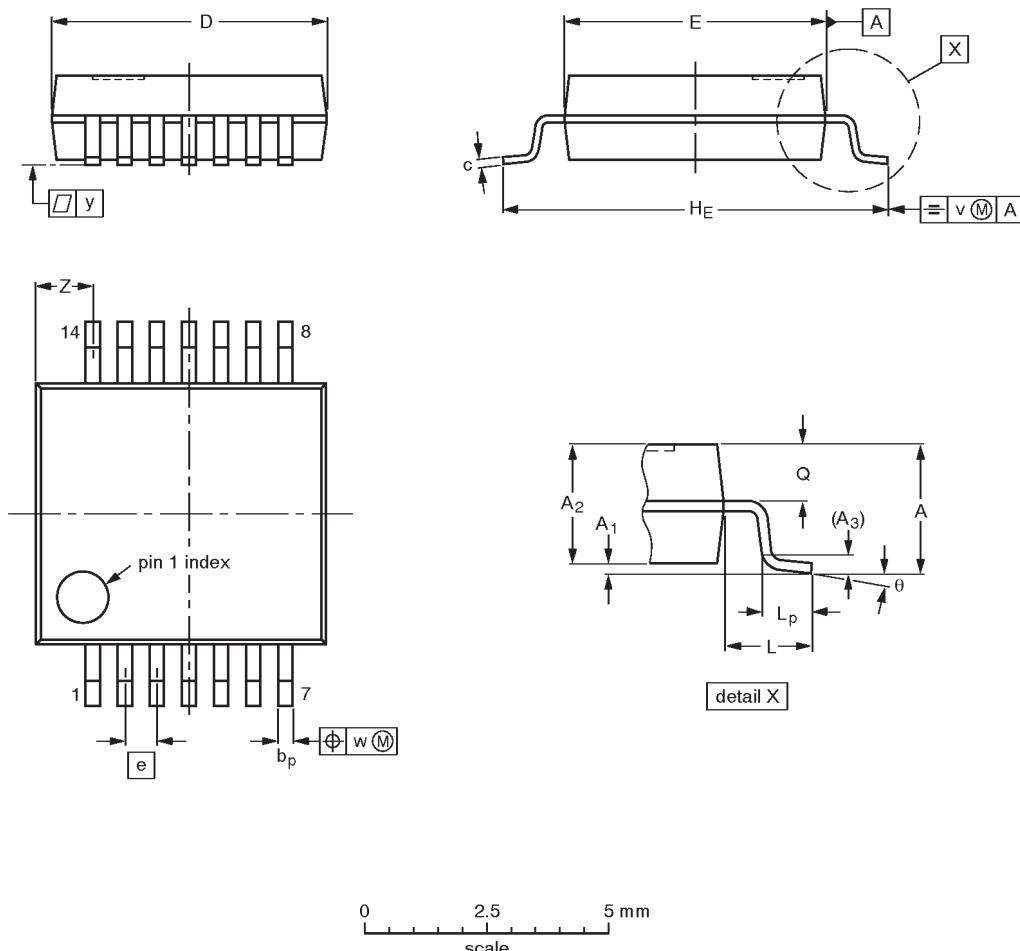
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT108-1	076E06S	MS-012AB				-95-01-23 97-05-22

Triple 3-input NAND gate

74ABT10

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	2.0 0.05	0.21 1.65	1.80	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

- Plastic or metal protrusions of 0.25 mm maximum per side are not included.

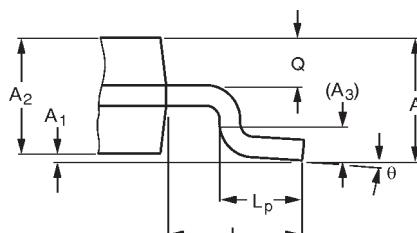
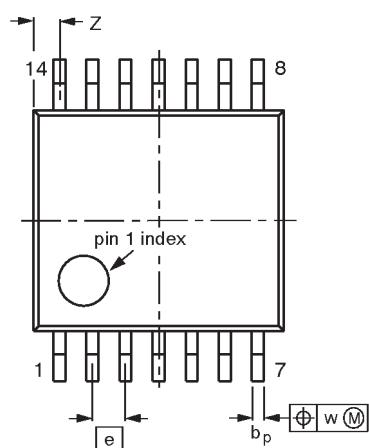
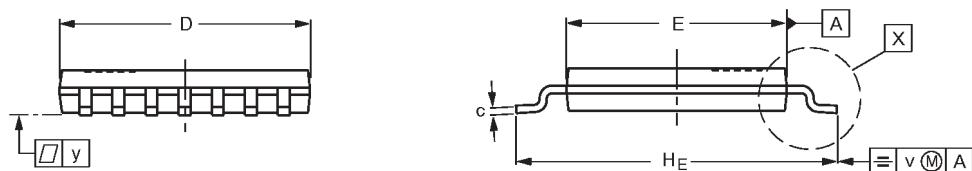
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT337-1		MO-150AB				95-02-04 96-01-18

Triple 3-input NAND gate

74ABT10

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



0 2.5 5 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1.10 0.05	0.15 0.080	0.95	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT402-1		MO-153				-94-07-12 95-04-04

Triple 3-input NAND gate

74ABT10

DEFINITIONS

Data Sheet Identification	Product Status	Definition
<i>Objective Specification</i>	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.
<i>Preliminary Specification</i>	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
<i>Product Specification</i>	Full Production	This data sheet contains Final Specifications. Philips Semiconductors reserves the right to make changes at any time without notice, in order to improve design and supply the best possible product.

Philips Semiconductors and Philips Electronics North America Corporation reserve the right to make changes, without notice, in the products, including circuits, standard cells, and/or software, described or contained herein in order to improve design and/or performance. Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified. Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

LIFE SUPPORT APPLICATIONS

Philips Semiconductors and Philips Electronics North America Corporation Products are not designed for use in life support appliances, devices, or systems where malfunction of a Philips Semiconductors and Philips Electronics North America Corporation Product can reasonably be expected to result in a personal injury. Philips Semiconductors and Philips Electronics North America Corporation customers using or selling Philips Semiconductors and Philips Electronics North America Corporation Products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors and Philips Electronics North America Corporation for any damages resulting from such improper use or sale.

Philips Semiconductors
811 East Arques Avenue
P.O. Box 3409
Sunnyvale, California 94088-3409
Telephone 800-234-7381

Philips Semiconductors and Philips Electronics North America Corporation register eligible circuits under the Semiconductor Chip Protection Act.
 © Copyright Philips Electronics North America Corporation 1995

All rights reserved. Printed in U.S.A.

(print code)

Date of release: July 1994

Document order number:

9397-750-04851